

Docket No. 248412US99DIV

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

IN RE APPLICATION OF: Jamal RAMDANI, et al.

SERIAL NO: 10/767,998

GAU: 2815

FILED: February 2, 2004

EXAMINER: BAUMEISTER

FOR: SEMICONDUCTOR STRUCTURE, SEMICONDUCTOR DEVICE, COMMUNICATING DEVICE, INTEGRATED CIRCUIT, AND PROCESS FOR FABRICATING THE SAME

**INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97**

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

**REFERENCES**

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, and copies were submitted in Application Serial No. 09/808,888 according to the attached copy of a Granted Petition. This application contains related subject matter.
- ☒ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

**RELATED CASES**

- ☐ Attached is a list of applicant's pending application(s), published application(s) or issued patent(s) which may be related to the present application. In accordance with the waiver of 37 CFR 1.98 dated September 21, 2004, copies of the cited pending applications are not provided. Cited published and/or issued patents, if any, are listed on the attached PTO form 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

**CERTIFICATION**

- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

**DEPOSIT ACCOUNT**

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,  
MAIER & NEUSTADT, P.C.

Richard L. Treanor

Registration No. 36,379

10/26/2004 EAREGAY1 00000047 10767998

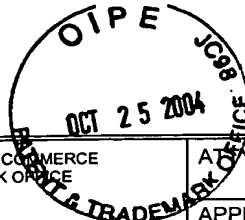
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Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTORNEY DOCKET NO. 248412US99DIV		SERIAL NO. 10/767,998	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Jamal RAMDANI, et al.			
				FILING DATE February 2, 2004		GROUP 2815	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	3,802,967	04/09/74	Ladany et al.			
	AB	4,174,422	11/13/79	Matthews et al.			
	AC	4,404,265	09/13/83	Manasevit			
	AD	4,482,906	11/13/84	Hovel et al.			
	AE	4,523,211	06/11/85	Morimoto et al.			
	AF	4,661,176	04/28/87	Manasevit			
	AG	4,793,872	12/27/88	Meunier et al.			
	AH	4,846,926	07/11/89	Kay et al.			
	AJ	4,855,249	06/08/89	Akasaki et al.			
	AI	4,891,091	01/02/90	Shastri			
	AK	4,912,087	03/27/90	Aslam et al.			
	AL	4,928,154	05/22/90	Umeno et al.			
	AM	4,963,949	10/16/90	Wanlass et al.			
	AN	5,141,894	08/25/92	Bisaro et al.			
	AO	5,159,413	10/27/92	Calviello et al.			
	AP	5,173,474	12/22/92	Connell et al.			
	AQ	5,221,367	06/22/93	Chisholm et al.			
	AR	5,225,031	07/06/93	McKee et al.			
	AS	5,358,925	10/25/94	Neville Connell et al.			
	AT	5,393,352	02/28/95	Summerfelt			
	AU	5,418,216	05/23/95	Fork			
	AV	5,450,812	09/19/95	McKee et al.			
	AW	5,478,653	12/26/95	Guenzer			
	AX	5,482,003	01/09/96	McKee et al.			
	AY	5,514,484	05/07/96	Nashimoto			
	AZ	5,556,463	09/17/96	Guenzer			
	BA	5,588,995	12/31/96	Sheldon			
	BB	5,670,798	09/23/97	Schetzina			
	BC	5,733,641	03/31/98	Fork et al.			
	BD	5,735,949	04/07/98	Mantl et al.			
	BE	5,741,724	04/21/98	Ramdani et al.			
	BF	5,810,923	09/22/98	Yano et al.			
	BG	5,830,270	11/03/98	McKee et al.			
	BH	5,912,068	06/15/99	Jia			
	BI	6,020,222	02/01/00	Wollesen			
	BJ	6,045,626	04/04/00	Yano et al.			
	BK	6,064,078	05/16/00	Northrup et al.			
	BL	6,064,092	05/16/00	Park			
	BM	6,096,584	08/01/00	Ellis-Monaghan et al.			
	BN	6,103,008	08/15/00	McKee et al.			
	BO	6,136,666	10/24/00	So			
	BP	6,174,755	01/16/01	Manning			
	BQ	6,180,486	01/30/01	Leobandung et al.			

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	CA	3,766,370	10/16/73	Walther			
	CB	4,006,989	02/08/77	Andringa			
	CC	4,284,329	08/18/81	Smith et al.			
	CD	4,777,613	10/11/98	Shahan et al.			
	CE	4,802,182	01/31/89	Thornton et al.			
	CF	4,882,300	11/21/89	Inoue et al.			
	CG	4,896,194	01/23/90	Suzuki			
	CH	4,999,842	03/12/91	Huang et al.			
	CI	5,081,062	01/14/92	Vasudev et al.			
	CJ	5,155,658	10/13/92	Inam et al.			
	CK	5,248,564	09/28/93	Ramesh			
	CL	5,260,394	11/09/93	Tazaki et al.			
	CM	5,270,298	12/14/93	Ramesh			
	CN	5,286,985	02/15/94	Taddiken			
	CO	5,310,707	05/10/94	Oishi et al.			
	CP	5,326,721	07/05/94	Summerfelt			
	CQ	5,404,581	04/04/95	Honjo			
	CR	5,418,389	05/23/95	Watanabe			
	CS	5,436,759	07/25/95	Dijai et al.			
	CT	5,576,879	11/19/96	Nashimoto			
	CU	5,606,184	02/25/97	Abrokwah, et al.			
	CV	5,640,267	06/17/97	May et al.			
	CW	5,674,366	10/07/97	Hayashi et al.			
	CX	5,729,641	03/17/98	Chandonnet et al.			
	CY	5,790,583	08/04/98	Ho			
	CZ	5,825,799	10/20/98	Ho et al.			
	DA	5,857,049	01/05/99	Beranek et al.			
	DB	5,874,860	02/23/99	Brunel et al.			
	DC	5,926,496	07/20/99	Ho et al.			
	DD	5,937,285	08/10/99	Abrokwah, et al.			
	DE	5,981,400	11/09/99	Lo			
	DF	5,990,495	11/23/99	Ohba			
	DG	6,002,375	12/14/99	Corman et al.			
	DH	6,008,762	12/28/99	Nghiem			
	DI	6,055,179	04/25/00	Koganei et al.			
	DJ	6,107,653	08/22/00	Fitzgerald			
	DK	6,113,690	09/05/00	Yu et al.			
	DL	6,114,996	09/05/00	Nghiem			
	DM	6,121,642	09/19/00	Newns			
	DN	6,128,178	10/03/00	Newns			
	DO	6,143,072	11/07/00	McKee et al.			
	DP	6,184,144	02/06/01	Lo			
	DQ	6,222,654	04/24/01	Frigo			

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	EA	4,484,332	11/20/84	Hawrylo			
	EB	4,815,084	03/21/89	Scifres et al.			
	EC	4,876,219	10/24/89	Eshita et al.			
	ED	4,963,508	10/16/90	Umeno et al.			
	EE	5,060,031	10/22/91	Abrokwah, et al.			
	EF	5,063,166	11/05/91	Mooney et al.			
	EG	5,116,461	05/26/92	Lebby et al.			
	EH	5,127,067	06/30/92	Delcoco et al.			
	EI	5,144,409	09/01/92	Ma			
	EJ	5,293,050	03/08/94	Chapple-Sokol et al			
	EK	5,356,831	10/18/94	Calviello et al.			
	EL	5,391,515	02/21/95	Kao et al.			
	EM	5,442,191	08/15/95	Ma			
	EN	5,444,016	08/22/95	Abrokwah, et al.			
	EO	5,480,829	01/02/96	Abrokwah, et al.			
	EP	5,528,414	06/18/96	Oakley			
	EQ	5,614,739	03/25/97	Abrokwah et al.			
	ER	5,729,394	03/17/98	Sevier et al.			
	ES	5,731,220	03/24/98	Tsu et al.			
	ET	5,764,676	06/09/98	Paoli et al.			
	EU	5,777,762	07/07/98	Yamamoto			
	EV	5,778,018	07/07/98	Yoshikawa et al.			
	EW	5,778,116	07/07/98	Tomich			
	EX	5,801,105	09/01/98	Yano et al.			
	EY	5,828,080	10/27/98	Yano et al.			
	EZ	5,858,814	01/12/99	Goossen et al.			
	FA	5,861,966	01/19/99	Ortel			
	FB	5,883,996	03/16/99	Knapp et al.			
	FC	5,995,359	11/30/99	Klee et al.			
	FD	6,058,131	05/02/00	Pan			
	FE	6,137,603	10/24/00	Henmi			
	FF	6,146,906	11/14/00	Inoue et al.			
	FG	6,173,474	01/16/01	Conrad			
	FH	6,180,252	01/30/01	Farrell et al.			
	FI	4,242,595	12/30/0	Lehovec			
	FJ	4,398,342	08/16/83	Pitt et al.			
	FK	4,424,589	01/03/84	Thomas et al.			
	FL	4,876,208	10/24/89	Gustafson et al.			
	FM	4,482,422	11/84	McGinn et al.			
	FN	4,667,088	05/19/87	Kramer			
	FO	4,772,929	09/20/88	Manchester et al.			
	FP	4,841,775	06/27/89	Ikeda et al.			
	FQ	4,845,044	07/04/89	Ariyoshi et al.			

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	GA	4,868,376	09/19/89	Lessin et al.			
	GB	4,885,376	12/05/89	Verkade			
	GC	4,888,202	12/89	Murakami et al.			
	GD	4,891,091	12/90	Wanlass et al.			
	GE	5,051,790	09/24/91	Hammer			
	GF	5,055,445	10/08/91	Belt et al.			
	GG	5,081,519	11/14/92	Nishimura et al.			
	GH	5,143,854	09/01/92	Pirung et al.			
	GI	5,185,589	02/09/93	Krishnaswamy et al.			
	GJ	5,191,625	03/02/93	Gustavsson			
	GK	5,194,397	03/16/93	Cook et al.			
	GL	5,208,182	05/04/93	Narayan et al.			
	GM	5,216,729	06/01/93	Berger et al.			
	GN	5,314,547	05/24/94	Heremans et al.			
	GO	5,352,926	10/04/94	Andrews			
	GP	5,356,509	10/18/94	Terranova et al.			
	GQ	5,371,734	12/06/94	Fischer			
	GR	5,372,992	12/94	Itozaki et al.			
	GS	5,405,802	04/11/95	Yamagata et al.			
	GT	5,442,561	08/15/95	Yoshizawa et al.			
	GU	5,453,727	09/26/95	Shibasaki et al.			
	GV	5,466,631	11/14/95	Ichikawa et al.			
	GW	5,473,047	12/05/95	Shi			
	GX	5,473,171	12/95	Summerfelt			
	GY	5,479,033	12/26/95	Baca et al.			
	GZ	5,486,406	01/23/96	Shi			
	HA	5,491,461	02/13/96	Partin et al.			
	HB	5,492,859	02/20/96	Sakaguchi et al.			
	HC	5,494,711	02/27/96	Takeda et al.			
	HD	5,504,035	04/02/96	Rostoker et al.			
	HE	5,504,183	04/02/96	Shi			
	HF	5,511,238	04/23/96	Bayraktaroglu			
	HG	5,512,773	04/96	Wolf et al.			
	HH	5,515,047	05/07/96	Yamakido et al.			
	HI	5,515,810	05/14/96	Yamashita et al.			
	HJ	5,519,235	05/96	Ramesh			
	HK	5,549,977	08/96	Jin et al.			
	HL	5,551,238	09/03/96	Prueitt			
	HM	5,552,547	09/03/96	Shi			
	HN	5,589,284	12/31/96	Summerfelt et al.			
	HO	5,602,418	02/11/97	Imai et al.			
	HP	5,633,724	05/27/97	King et al.			

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	IA	5,650,646	07/22/97	Summerfelt			
	IB	5,656,382	08/12/97	Nashimoto			
	IC	5,659,180	08/19/97	Shen et al.			
	ID	5,661,112	08/26/97	Hatta et al.			
	IE	5,679,965	11/95	Schetzina			
	IF	5,725,641	03/10/98	MacLeod			
	IG	5,745,631	04/28/98	Reinker			
	IH	5,776,621	07/07/98	Nashimoto			
	II	5,777,350	07/07/98	Nakamura et al.			
	IJ	5,789,845	08/04/98	Wadaka et al.			
	IK	5,792,569	08/11/98	Sun et al.			
	IL	5,792,679	08/11/98	Nakato			
	IM	5,796,648	08/18/98	Kawakubo et al.			
	IN	5,801,072	09/01/98	Barber			
	IO	5,812,272	09/22/98	King et al.			
	IP	5,814,583	09/98	Itozaki et al.			
	IQ	5,825,055	10/20/98	Summerfelt			
	IR	5,827,755	10/27/98	Yonchara et al.			
	IS	5,833,603	11/10/98	Kovacs et al.			
	IT	5,838,035	11/17/98	Ramesh			
	IU	5,844,260	12/01/98	Ohuri			
	IV	5,846,846	12/08/98	Suh et al.			
	IW	5,863,326	01/26/99	Nause et al.			
	IX	5,872,493	02/16/99	Ella			
	IY	5,879,956	03/99	Seon et al.			
	IZ	5,880,452	03/09/99	Plesko			
	JA	5,883,564	03/16/99	Partin			
	JB	5,907,792	05/25/99	Droopad et al.			
	JC	5,937,274	08/10/99	Kondow et al.			
	JD	5,948,161	09/07/99	Kizuki			
	JE	5,959,879	09/28/99	Koo			
	JF	5,966,323	10/99	Chen et al.			
	JG	5,987,011	11/16/99	Toh			
	JH	6,022,140	02/08/00	Fraden et al.			
	JI	6,022,410	02/08/00	Yu et al.			
	JJ	6,023,082	02/08/00	McKee et al.			
	JK	6,028,853	02/22/00	Haartsen			
	JL	6,049,702	04/11/00	Tham et al.			
	JM	6,078,717	06/20/00	Nashimoto et al			
	JN	6,088,216	07/00	Laibowitz et al.			
	JO	6,090,659	07/00	Laibowitz et al.			
	JP	6,107,721	08/22/00	Lakin			
	JQ	6,153,010	11/28/00	Kiyoku et al			

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	KA	6,153,454	11/28/00	Krivokapic			
	KB	6,191,011	02/01	Gilboa et al.			
	KC	6,204,737	03/20/01	Ella			
	KD	6,224,669	05/01/01	Yi et al.			
	KE	6,225,051	05/01/01	Sugiyama et al.			
	KF	6,241,821	06/05/01	Yu et al.			
	KG	6,265,749	07/24/01	Gardner et al.			
	KH	6,313,486	11/01	Kencke et al.			
	KI	6,316,832	11/13/01	Tsuzuki et al.			
	KJ	2002/0008234	01/02	Emrick			
	KK	3,670,213	06/13/72	Nakawaga et al.			
	KL	4,756,007	07/05/88	Qureshi et al.			
	KM	4,773,063	09/20/88	Hunsperger et al.			
	KN	5,394,489	02/28/95	Koch			
	KO	5,406,202	04/11/95	Mehrgardt et al.			
	KP	5,528,067	06/18/96	Farb et al.			
	KQ	5,572,052	11/05/96	Kashihara et al.			
	KR	5,767,543	06/16/98	Ooms et al.			
	KS	6,175,497	01/16/01	Tseng et al.			
	KT	6,197,503	03/06/01	Vo-Dinh et al.			
	KU	6,248,459	06/19/01	Wang et al.			
	KV	6,252,261	06/26/01	Usui et al.			
	KW	6,255,198	07/03/01	Linthicum et al.			
	KX	6,268,269	07/31/01	Lee et al.			
	KY	6,291,319	09/18/01	Yu et al.			
	KZ	6,316,785	11/13/01	Nunoue et al.			
	LA	6,343,171	01/29/02	Yoshimura et al.			
	LB	4,965,649	10/23/90	Zanio et al.			
	LC	6,253,649	05/01	Kawahara et al.			
	LD	6,211,096	04/01	Allman et al.			
	LE	6,239,449	05/29/01	Fafard et al.			
	LF	2001/0013313	08/16/01	Droopad et al.			
	LG	6,184,044	02/06/01	Sone et al.			
	LH	6,011,646	01/04/00	Mirkarimi et al.			
	LI	5,227,196	07/13/93	Itoh			
	LJ	6,150,239	11/21/00	Goesele et al.			
	LK	5,441,577	08/15/95	Sasaki et al.			
	LL	4,459,325	07/10/84	Nozawa et al.			
	LM	4,392,297	07/12/83	Little			
	LN	4,289,920	09/15/81	Hovel			
	LO	5,281,834	01/25/94	Cambou et al.			
	LP	4,901,133	02/13/90	Curran et al.			
	LQ	5,514,904	05/07/96	Onga et al.			

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	MA	5,553,089	09/03/96	Seki et al.			
	MB	5,528,057	06/18/96	Yanagase et al.			
	MC	6,229,159	05/08/01	Suzuki			
	MD	4,748,485	05/31/88	Vasudev			
	ME	4,984,043	01/08/91	Vinal			
	MF	5,754,319	05/19/98	Van De Voorde et al.			
	MG	6,108,125	08/22/00	Yano			
	MH	5,073,981	12/17/91	Giles et al.			
	MI	5,140,651	08/18/92	Soref et al.			
	MJ	5,610,744	03/11/97	Ho et al.			
	MK	6,362,017	03/26/02	Manabe et al.			
	ML	6,242,686	06/05/01	Kishimoto et al.			
	MM	5,689,123	11/18/97	Major et al.			
	MN	5,670,800	09/23/97	Nakao et al.			
	MO	5,067,809	11/26/91	Tsubota			
	MP	5,596,205	01/21/97	Reedy et al.			
	MQ	6,175,555	01/16/01	Hoole			
	MR	5,357,122	10/18/94	Okubora et al.			
	MS	4,084,130	04/11/78	Holton			
	MT	6,093,302	07/25/00	Montgomery			
	MU	6,372,813	04/16/02	Johnson et al.			
	MV	5,608,046	03/04/97	Cook et al.			
	MW	5,955,591	09/21/99	Imbach et al.			
	MX	6,022,963	02/08/00	McGall et al.			
	MY	6,083,697	07/04/00	Beecher et al.			
	MZ	5,063,081	11/05/91	Cozzette et al.			
	NA	5,479,317	12/26/95	Ramesh			
	NB	5,306,649	04/26/94	Hebert			
	NC	5,962,069	10/05/99	Schindler et al.			
	ND	5,541,422	07/30/96	Wolf et al.			
	NE	5,873,977	02/23/99	Desu et al.			
	NF	5,538,941	07/23/96	Findikoglu et al.			
	NG	6,046,464	04/04/00	Schetzina			
	NH	6,235,145	05/22/01	Li et al.			
	NI	5,610,744	03/11/97	Ho et al.			
	NJ	5,280,013	01/18/94	Newman et al.			
	NK	6,348,373 B1	02/19/02	Ma et al.			
	NL	6,339,664 B1	01/15/02	Farjady et al.			
	NM	4,439,014	03/27/84	Stacy et al.			
	NN	4,889,402	12/26/89	Reinhart			
	NO	5,963,291	10/05/99	Wu et al.			
	NP	6,011,641	01/04/00	Shin et al.			
	NQ	6,340,788 B1	01/22/02	King et al.			



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	OA	5,807,440	09/15/98	Kubota et al.			
	OB	4,681,982	07/21/87	Yoshida			
	OC	4,629,821	12/16/86	Bronstein-Bonte et al.			
	OD	4,452,720	06/05/84	Harada et al.			
	OE	3,935,031	01/27/76	Adler			
	OF	5,760,426	06/02/98	Marx et al.			
	OG	5,053,835	10/01/91	Horikawa et al.			
	OH	6,326,645 B1	12/04/01	Kadota			
	OI	5,770,887	06/23/98	Tadatomo et al.			
	OJ	6,372,356 B1	04/16/02	Thornton et al.			
	OK	4,774,205	09/27/88	Choi et al.			
	OL	6,359,330 B1	03/19/02	Goudard			
	OM	5,312,765	05/17/94	Kanber			
	ON	5,734,672	03/31/98	McMinn et al.			
	OO	6,367,699 B2	04/09/02	Ackley			
	OP	5,530,235	06/25/96	Stefik et al.			
	OQ	5,623,552	04/22/97	Lane			
	OR	5,481,102	01/02/96	Hazelrigg, Jr.			
	OS	6,134,114	10/17/00	Ungermann et al.			
	OT	5,984,190	11/16/99	Nevill			
	OU	5,789,733	08/04/98	Jachimowicz et al.			
	OV	5,753,300	05/19/98	Wessels et al.			
	OW	6,208,453	03/27/01	Wessels et al.			
	OX	5,886,867	03/23/99	Chivukula et al.			
	OY	5,028,976	07/02/91	Ozaki et al.			
	OZ	5,869,845	02/09/99	Vander Wagt et al.			
	PA	5,596,214	01/21/97	Endo			
	PB	6,391,674 B2	05/21/02	Ziegler			
	PC	6,275,122 B1	08/14/01	Speidell et al.			
	PD	6,238,946 B1	05/29/01	Ziegler			
	PE	6,210,988 B1	04/03/01	Howe et al.			
	PF	6,392,257	05/21/02	Ramdani et al.			
	PG	4,442,590	04/17/84	Stockton et al.			
	PH	5,603,764	02/18/97	Matsuda et al.			
	PI	6,087,681	06/11/00	Shakuda			
	PJ	5,132,648	07/21/92	Trinh et al.			
	PK	6,427,066	07/30/02	Grube			
	PL	2002/0072245	06/13/02	Ooms et al.			
	PM	6,278,138 B1	08/21/01	Suzuki			
	PN	5,888,296	03/30/99	Ooms et al.			
	PO	5,198,269	03/30/93	Swartz et al.			
	PP	2002/0030246	03/14/02	Eisenbeiser et al.			
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	QB	5,569,953	10/29/96	Kikkawa et al.			
	QC	5,834,362	11/10/98	Miyagaki et al.			
	QD	6,248,621 B1	06/19/01	Wilk et al.			
	QE	5,266,355	11/30/93	Wernberg et al.			
	QF	6,277,436 B1	08/21/01	Stauf et al.			
	QG	6,039,803	03/21/00	Fitzgerald et al.			
	QH	5,619,051	04/08/97	Endo			
	QI	5,420,102	05/30/95	Harshavardhan et al.			
	QJ	5,210,763	05/11/93	Lewis et al.			
	QK	5,103,494	04/07/92	Mozer			
	QL	4,594,000	06/10/86	Falk et al.			
	QM	4,297,656	10/27/81	Pan			
	QN	5,244,818	09/14/93	Jokers et al.			
	QO	6,048,751	04/11/00	D'Asaro et al.			
	QP	5,484,664	01/16/96	Kitahara et al.			
	QQ	5,780,311	07/14/98	Beasom et al.			
	QR	6,438,281 B1	08/20/02	Tsukamoto et al.			
	QS	5,399,898	03/21/95	Rostoker			
	QT	6,271,619	08/07/01	Yamada et al.			
	QU	5,334,556	08/02/94	Guldi			
	QV	4,910,164	03/20/90	Shichijo			
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	QX	6,121,647	09/19/00	Yano et al.			
	QY	6,306,668 B1	10/23/01	McKee et al.			
	QZ	6,143,366	11/07/00	Lu			
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	RL	5,130,762	07/14/92	Kulick			
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	RN	6,389,209 B1	05/14/02	Suhir			
	RO	5,163,118	11/10/92	Lorenzo et al.			
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	SB	5,395,663	03/07/95	Tabata et al.			
	SC	4,146,297	03/27/79	Alferness et al.			
	SD	5,452,118	09/19/95	Maruska			
	SE	5,889,296	03/30/99	Imamura et al.			
	SF	6,300,615 B1	10/09/01	Shinohara et al.			
	SG	6,232,910 B1	05/15/01	Bell et al.			
	SH	5,686,741	11/11/97	Ohori et al.			
	SI	4,959,702	09/25/90	Moyer et al			
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	SK	6,410,947 B1	06/25/02	Wada			
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	SM	6,461,927 B1	10/08/02	Mochizuki et al.			
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	SW	6,312,819 B1	11/06/01	Jia et al.			
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	TJ	5,668,048	09/16/97	Kondo et al.			
	TK	5,852,687	12/22/98	Wickham			
	TL	5,122,852	06/16/92	Chan et al.			
	TM	5,173,835	12/22/92	Cornett et al.			
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	TO	6,139,483	10/31/00	Seabaugh et al.			
	TP	5,283,462	02/01/94	Stengel			
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	UB	5,427,988	06/27/95	Sengupta et al.			
	UC	6,297,842 B1	10/02/01	Koizumi et al.			
	UD	5,682,046	10/28/97	Takahashi et al.			
	UE	5,181,085	01/19/93	Moon et al.			
	UF	6,051,858	04/18/00	Uchida et al.			
	UG	6,013,553	01/11/00	Wallace et al.			
	UH	4,872,046	10/03/89	Morkoc et al.			
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	UL	5,438,584	08/01/95	Paoli et al.			
	UM	4,503,540	03/05/85	Nakashima et al.			
	UN	5,373,166	12/13/94	Buchan et al.			
	UO	6,278,137 B1	08/21/01	Shimoyama et al.			
	UP	5,623,439	04/22/97	Gotoh et al.			
	UQ	4,981,714	01/01/91	Ohno et al.			
	UR	6,194,753 B1	02/27/01	Seon et al.			
	US	6,326,637 B1	12/04/01	Parkin et al.			
	UT						
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	AAA	0 250 171	12/23/87	EP	X		
	AAB	0 342 937	11/23/89	EP	X		
	AAC	0 455 526	06/11/91	EP	X		
	AAD	0 602 568	06/22/94	EP	X		
	AAE	0 607 435	07/27/94	EP	X		
	AAF	1 001 468	05/17/00	EP	X		
	AAG	0 514 018	11/19/92	EP	X		
	AAH	0 999 600	05/10/00	EP	X		
	AAI	1 319 311	06/04/70	Great Britain	X		
	AAJ	5-291299	11/05/93	Japan w/English Abstract	X		
	AAK	11-238683	08/31/99	Japan	X		
	AAL	11-260835	09/24/99	Japan w/English Abstract	X		
	AAM	HEI 2-391	01/05/90	Japan w/English Abstract	X		
	AAN	5-48072	02/26/93	Japan w/English Abstract	X		
	AAO	52-88354	07/23/77	Japan w/English Abstract	X		
	AAP	54-134554	10/19/79	Japan w/English Abstract	X		
	AAQ	55-87424	07/02/80	Japan w/English Abstract	X		
	AAR	61-108187	05/26/86	Japan w/English Abstract	X		
	AAS	6-232126	08/19/94	Japan	X		
	AAT	6-291299	10/18/94	Japan w/English Abstract	X		
	AAU	63-34994	02/15/88	Japan w/English Abstract	X		
	AAV	63-131104	06/03/88	Japan w/English Abstract	X		
	AAW	63-198365	08/17/88	Japan w/English Abstract	X		
	AAX	10-321943	12/04/98	Japan	X		
	AAY	6-334168	12/02/94	Japan	X		
	AAZ	WO 99/63580	12/09/99	WIPO	X		
	ABA	WO 99/14804	03/25/99	WIPO	X		
	ABB	WO 97/45827	12/04/97	WIPO			
	ABC	WO 99/19546	04/22/99	WIPO			
	ABD	WO 00/33363	06/08/00	WIPO			
	ABE	WO 00/48239	08/17/00	WIPO			
	ABF	WO 99/14797	03/25/99	WIPO			
	ABG	GB 2 335 792	09/29/99	Great Britain			
	ABH	1 109 212	06/20/01	Europe			
	ABI	DE 197 12 496	10/30/97	Germany		X	
	ABJ	60-212018	10/24/85	Japan w/English Abstract			
	ABK	60-210018	10/22/85	Japan w/English Abstract			
	ABL	WO 92/10875	06/25/92	WIPO			
	ABM	0 682 266	11/15/95	Europe			
	ABN	3-41783	02/91	Japan (English Abstract only)			
	ABO	0 581 239	02/02/94	Europe			
	ABP	0812494	01/16/96	Japan			
	ABQ	2 000 1645	06/16/00	Japan			

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	BAA	1 043 426	10/11/00	Europe			
	BAB	2000-068466	03/00	Japan (Abstract)			
	BAC	64-50575	02/27/89	Japan			
	BAD	WO 98/05807	01/12/98	WIPO			
	BAE	WO 94/03908	02/17/94	WIPO			
	BAF	WO 01/33585	05/10/01	WIPO			
	BAG	1-102435	04/20/89	Japan w/English Abstract			
	BAH	52-135684	11/12/77	Japan (English Abstract)			
	BAI	02051220	02/21/90	Japan (English Abstract)			
	BAJ	11135614	05/21/99	Japan (w/English Abstract)			
	BAK	64-52329	02/28/89	Japan (w/English Abstract)			
	BAL	10-256154	09/25/98	Japan (w/English Abstract)			
	BAM	DE 196 07 107	08/28/97	Germany			xx
	BAN	10-303396	11/13/98	Japan (w/English Abstract)			
	BAO	58-213412	12/12/83	Japan w/English Abstract			
	BAP	0 964 259	12/15/99	Europe			
	BAQ	0 875 922	11/04/98	Europe			
	BAR	61-63015	04/01/86	Japan w/English Abstract			
	BAS	11340542	12/10/99	Japan (English Abstract)			
	BAT	WO 01/37330	05/25/01	WIPO			
	BAU	0 331 467	09/06/89	Europe			
	BAV	WO 00/16378	03/23/00	WIPO			
	BAW	0 926 739	06/30/99	Europe			
	BAX	0 964 453	12/15/99	Europe			
	BAY	5-152529	06/18/93	Japan w/English Abstract			
	BAZ	9-67193	03/11/97	Japan w/English Abstract			
	BBA	9-82913	03/28/97	Japan w/English Abstract			
	BBB	0 309 270	03/29/89	Europe			
	BBC	EP 0 957 522	11/17/99	Europe			
	BBD	EP 0 810 666	12/03/97	Europe			
	BBE	1-179411	07/17/89	Japan w/English Abstract			
	BBF	DE 100 17 137	10/26/00	GERMANY			
	BBG	WO 02 01648	01/03/02	WIPO			
	BBH	WO 02/33385 A2	04/25/02	WIPO			
	BBI	WO 01/59814 A2	08/16/01	WIPO			
	BBJ	WO 02/09160 A2	01/31/02	WIPO			
	BBK	WO 00/06812	02/10/00	WIPO			
	BBL	0 483 993	05/06/92	Europe			
	BBM	0 538 611	04/28/93	Europe			
	BBN	WO 01/59820 A1	08/16/01	WIPO			
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	CAA	52-89070	07/26/77	Japan	xx		
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	CAC	WO 02/03113	01/10/02	WIPO			
	CAD	WO 02/03467	01/10/02	WIPO			
	CAE	0 630 057	12/21/94	EUROPE			
	CAF	61-36981	02/21/86	Japan w/English Abstract			
	CAG	WO 93/07647	04/15/93	WIPO			
	CAH	2002-9366	01/11/02	Japan w/English Abstract			
	CAI	EP 0 881 669	12/02/98	Europe			
	CAJ	WO 02/03480	01/10/02	WIPO			
	CAK	WO 02/50879	06/27/02	WIPO			
	CAL	EP 0 777 379	06/04/97	Europe			
	CAM	WO 01/04943 A1	01/18/01	WIPO		XX	
	CAN	WO 02/47127 A2	06/13/02	WIPO			
	CAO	JP 58-075868	05/07/83	Japan w/English Abstract			
	CAP	EP 0 993 027	04/12/00	Europe			
	CAQ	EP 0 711 853	05/15/96	Europe			
	CAR	WO 98/20606	05/14/98	WIPO			
	CAS	EP 1 043 765	10/11/00	Europe			
	CAT	0 300 499	01/25/89	Europe			
	CAU	EP 1 085 319	03/21/01	Europe			
	CAV	WO 01/16395	03/08/01	WIPO			
	CAW	2000-351692	12/19/00	Japan w/English Abstract			
	CAX	03-188619	08/16/91	Japan (English Abstract only)			
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	CAZ	EP 0 884 767	12/16/98	Europe			
	CBA	06-069490	03/11/94	Japan (English Abstract only)			
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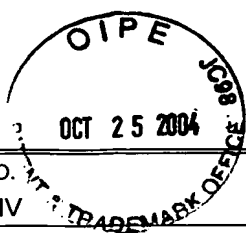
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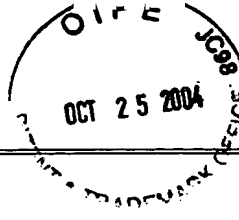
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	UV	5,998,781	12/07/99	Vawter et al.			
	UW	6,110,813	08/29/00	Ota et al.			
	UX	6,452,232 B1	09/17/02	Adan			
	UY	6,049,110	04/11/00	Koh			
	UZ	5,559,368	09/24/96	Hu et al.			
	VA	6,392,253 B1	05/21/02	Saxena			
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	VO	5,882,948	03/16/99	Jewell			
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	VQ	5,510,665	04/23/96	Conley			
	VR	4,804,866	02/14/89	Akiyama			
	VS	5,057,694	10/15/91	Idaka et al.			
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	VU	5,719,417	02/17/98	Roeder et al.			
	VV	5,998,819	12/07/99	Yokoyama et al.			
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	WA	5,905,571	05/18/99	Butler et al.			
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	XA	5,140,387	08/18/92	Okazaki et al.			
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	CBD	EP 0 860 913	08/26/95	EUROPE			
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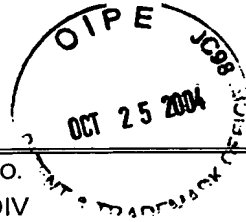
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	XP	6,181,920 B1	01/30/01	DENT ET AL			
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	XY	4,298,247	11/03/81	MICHELET ET AL			
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	YA	3,758,199	09/11/73	THAXTER			
	YB	6,362,558 B1	03/26/02	FUKUI			
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	YP	5,188,976	02/23/93	KUME ET AL			
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LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Jamal RAMDANI, et al.			
				FILING DATE February 2, 2004		GROUP 2815	
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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	YQ	6,501,121 B1	12/31/02	YU ET AL			
	YR	5,919,515	07/06/99	YANO ET AL			
	YS	5,238,877	08/24/93	RUSSELL			
	YT	5,540,785	07/30/96	DENNARD ET AL			
	YU	5,997,638	12/07/99	COPEL ET AL			
	YV	6,291,866	09/18/01	WALLACE			
	YW	5,365,477	11/15/94	COOPER, JR ET AL			
	YX	5,548,141	08/20/96	MORRIS ET AL			
	YY	2002/0021855	02/21/02	KIM			
	YZ	6,110,840	08/29/00	YU			
	ZA	5,667,586	09/16/97	EK ET AL			
	ZB	5,313,058	05/17/94	FRIEDERICH ET AL			
	ZC	5,315,128	05/24/94	HUNT ET AL			
	ZD	5,919,522	07/06/99	BAUM ET AL			
	ZE	4,843,609	06/27/89	OHYA ET AL			
	ZF	4,626,878	12/02/86	KUWANO ET AL			
	ZG	4,525,871	06/25/85	FOYT ET AL			
	ZH	3,818,451	06/18/74	COLEMAN			
	ZI	6,059,895	05/09/00	CHU ET AL			
	ZJ	4,447,116	05/08/84	KING ET AL			
	ZK	6,022,671	02/08/00	BINKLEY ET AL			
	ZL	5,754,714	05/19/98	SUZUKI ET AL			
	ZM	6,524,651 B2	02/25/03	GAN ET AL			
	ZN	6,355,945 B1	03/12/03	KADOTA ET AL			
	ZO	5,642,371	06/24/97	TOHYAMA ET AL			
	ZP	6,445,724 B2	09/03/02	ABELES			
	ZQ	5,753,934	05/19/98	YANO ET AL			
	ZR	6,326,667 B1	12/04/01	SUGIYAMA ET AL			
	ZS	6,051,874	04/18/00	MASUDA			
	ZT	5,166,761	11/24/92	OLSON ET AL			
	ZU	5,574,744	11/12/96	GAW ET AL			
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		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES                  NO		
	CCA	5-238894	09/17/93	JAPAN W/ENGLISH ABSTRACT			
	CCB	2 152 315	07/31/85	GREAT BRITAIN			
	CCC	2001-196892	07/19/01	JAPAN W/ENGLISH ABSTRACT			
	CCD	2000-278085	10/06/00	JAPAN (ENGLISH ABSTRACT)			
	CCE	WO 03/012874	02/13/03	WIPO			
	CCF	1 043 427	10/11/00	EUROPE			
	CCG	1 069 605	01/17/01	EUROPE			
	CCH	WO 02/099885	12/12/02	WIPO			
	CCI	10-269842	10/09/98	JAPAN W/ENGLISH ABSTRACT			
	CCJ	59066183	04/14/84	JAPAN (ENGLISH ABSTRACT)			
	CCK	03046384	02/27/91	JAPAN (ENGLISH ABSTRACT)			
	CCL	WO 02/11254	02/07/02	WIPO			
	CCM	0 494 514	07/15/92	EUROPE			
	CCN	0 247 722	12/02/87	EUROPE			
	CCO	1 037 272	09/20/00	EUROPE			
	CCP	59-073498	04/25/84	JAPAN (ENGLISH ABSTRACT)			
	CCQ	60-161635	08/23/85	JAPAN W/ENGLISH ABSTRACT			
	CCR	59-044004	03/12/84	JAPAN W/ENGLISH ABSTRACT			
	CCS	0 392 714	10/17/90	EUROPE			
	CCT						
	CCU						
	CCV						
	CCW						
	CCX						
	CCY						
	CCZ						
	CDA						
	CDB						
	CDC						
	CDD						
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	LLAA	Peter Weiss; "Speed demon gets hooked on silicon"; Science News Online; Sept. 15, 2001; pp. 1-3					
	LLAB	"Motorola Develops New Super-Fast Chip"; USA Today; Sept. 4, 2001					
	LLAC	Lori Valigra; "Motorola Lays GaAs on Si Wafer"; AsiaBizTech; Nov. 2001pp. 1-3					
	LLAD	"Holy Grail! Motorola Claims High-Yield GaAs Breakthrough"; Micromagazine.com (no date available); pp. 1-3					
	LLAE	Jong-Gul YOON; "Growth of Ferroelectric LiNbO <sub>3</sub> Thin Film on MgO-Buffered Si by the Sol-Gel Method"; Journal of the Korean Physical Society (Proc. Suppl.); Vol. 29, Nov. 1996; pp. S648-S651					
	LLAF	V. Bornand et al.; "Deposition of LiTaO <sub>3</sub> thin films by pyrosol process"; Thin Solid Films 304 (1997); pp.239-244					
	LLAG	R. Droopad et al.; "Development of high dielectric constant epitaxial oxides on silicon by molecular beam epitaxy"; Materials Science and Engineering B87 (2001); pp.292-296					
	LLAH	A.K. Sharma et al.; "Integration of Pb(Zr <sub>0.52</sub> Ti <sub>0.48</sub> )O <sub>3</sub> epilayers with Si by domain epitaxy"; Applied Physics Letters, Vol. 76, No. 11; March 13, 2000; pp. 1458-1460					
	LLAI	Dwight C. Streit et al; "High Reliability GaAs-AlGaAs HBT's by MBE with Be Base Doping and InGaAs Emitter Contacts"; 8179 IEEE Electron Device Letters; 12(1991) September, No. 9, New York, US					
	LLAJ	C. Y. Hung et al; "Piezoelectrically induced stress tuning of electro-optic devices"; 320 Applied Physics Letters; 59(1991) 30 December, No. 27, New York, US					
	LLAK	J. Piprek; "Heat Flow Analysis of Long-Wavelength VCSELs with Various DBR Materials"; University of Delaware, Materials Science, Newark, DE, 19716-3106; Oct. 31, 1994; pp. 286-287					
	LLAL	P. Mackowiak et al.; "Some aspects of designing an efficient nitride VCSEL resonator"; J. Phys. D: Appl. Phys. 34(2001); pp. 954-958					
	LLAM	M.R. Wilson et al.; GaAs-On-Si: A GaAs IC Manufacturer's Perspective"; GaAs IC Symposium, IEEE, 1988; pp. 243-246					
	LLAN	Y. Kitano et al.; "Thin film crystal growth of BaZrO <sub>3</sub> at low oxygen partial pressure"; Journal of Crystal Growth 243 (2002); pp. 164-169					
	LLAO	M.E. Hawley; et al; "Microstructural Study of Colossal Magneto-Resistive Films As a Function of Growth Temperature, As Deposited and Annealed"; 401, 1996; pp. 531-536					
	LLAP						
	LLAQ						
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	ZV	5,122,679	06/16/92	ISHII ET AL				
	ZW	6,232,806	05/15/01	WOESTE ET AL				
	ZX	5,430,397	07/04/95	ITOH ET AL				
	ZY	6,151,240	11/21/00	SUZUKI				
	ZZ	6,528,374	03/04/03	BOJARCZUK, JR ET AL				
	A1	6,589,887	07/08/03	DALTON ET AL				
	A2	5,064,781	11/12/91	CAMBOU ET AL				
	A3	2002/0052061	05/02/02	FITZGERALD				
	A4	5,696,392	12/09/97	CHAR ET AL				
	A5	5,986,301	11/16/99	FUKUSHIMA ET AL				
	A6	6,329,277	12/11/01	LIU ET AL				
	A7							
	A8							
	A9							
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		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO			
	CCS	WO 99/67882	12/29/99	WIPO				
	CCT	WO 95/02904	01/26/95	WIPO				
	CCU	WO 02/009150	01/31/02	WIPO				
	CCV	0 766 292	04/02/97	EUROPE				
	CCW	198 29 609	01/05/00	GERMANY				
	CCX	1 069 605	01/17/01	EUROPE				
	CCY	0 828 287	03/11/98	EUROPE				
	CCZ	1 176 230	01/30/02	EUROPE				
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)								
	LLAP	YI W. et al; "Mechanism of cleaning Si (100) surface using Sr and SrO for the growth of crystalline SrTiO/sub 2/films" Journal of Vacuum Science & Technology, Vol. 20, No. 4, July 2002 (2002-07) pp. 1402-1405						
	LLAQ	XIAMING HU et al; "Sr/Si template formation for the epitaxial growth of SrTiO/sub 3/on silicon" Materials Research Society Proceedings, Vol. 716, 2002, pp. 261-266						
	LLAR							
	LLAS					<input type="checkbox"/> Additional References sheet(s) attached		
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